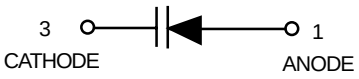
Silicon Pin Diode

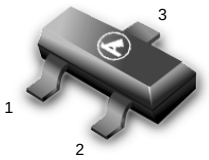
This device is designd primarily for VHF band switching applications but is also suitable for use in general-purpose switching circuits.Supplied in a surface Mount package.

- Rugged Pin Structure Coupled with Wirebond Construction for Optimum Reliability
- Low Capacitance—0.7pF Typ at VR=20Vdc
- Very Low Series Resistance at 100MHz—0.34Ohms(Typ)@IF=10mAdc



MMBV3401LT1

SILICON PIN SWITCHING DIODE



CASE 318–08, STYLE 6
SOT– 23 (TO–236AB)

MAXIMUM RATINGS(EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	20	Vdc
Forward power Dissipation @T_A = 25°C	P_D	200	mW
Derate above 25°C		2.0	mW/°C
Junction Temperature	T_J	+125	°C
Storage Temperature Range	T_{stg}	–55 to +150	°C

DEVICE MARKING

MMBV3401LT1=4D

ELECTRICAL CHARACTERISTICS(T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R=10μAdc)	$V_{(BR)R}$	35	—	—	Vdc
Diode Capacitance (V_R=20 Vdc)	C_T	—	—	1.0	pF
Series Resistance(figure5) (I_F=10mAdc,f=100MHz)	R_S	—	—	0.7	Ω
Reverse Voltage Leakage Current (V_R=15Vdc)	I_R	—	—	0.1	μAdc

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TYPICAL CHARACTERISTICS

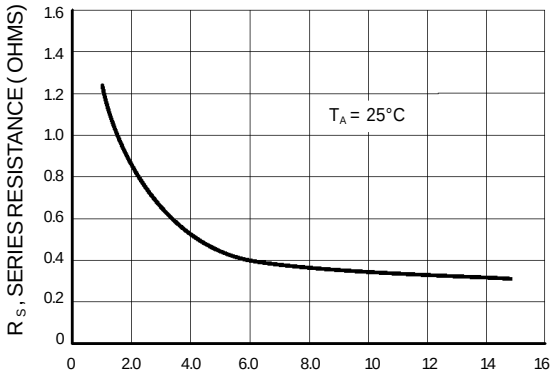

Figure 1. Series Resistance

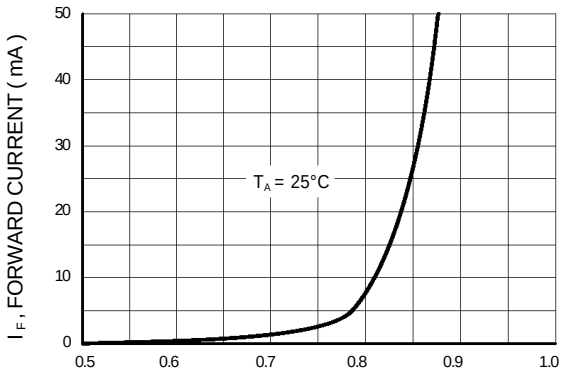

Figure 2. Forward Voltage

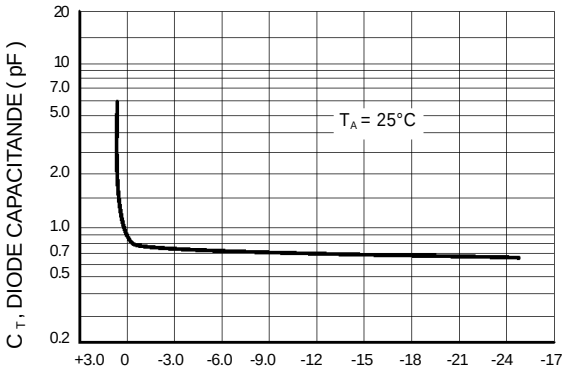

Figure 3. Diode Capacitance

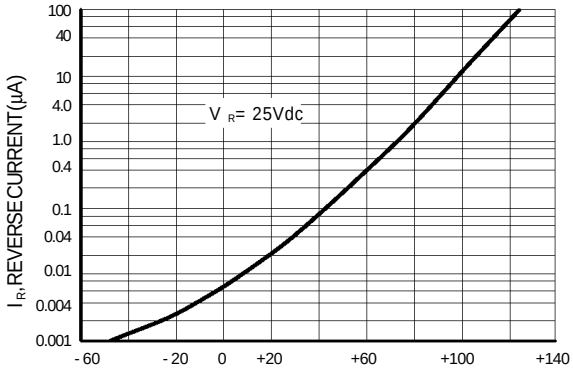

Figure 4. Leakage Current